Product data sheet

1. General description

Ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- Fast switching
- Guaranteed ESD capability
- · High thermal cycling performance
- Low on-state loss
- Low thermal resistance
- · Rugged: reverse voltage surge capability
- Soft recovery minimizes power-consuming oscillations

3. Applications

· Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Va | lues | | Unit |
|--------------------|---------------------------------|---|---------|-----|------|-------|------|
| Absolute | maximum rating | | | | | | |
| V_{RRM} | repetitive peak reverse voltage | | 100 | | | V | |
| I _{F(AV)} | average forward current | δ = 0.5 ; T _{mb} ≤ 128 °C; square-wave pulse; Fig. 1; Fig. 2 | 8 | | | А | |
| I _{FRM} | repetitive peak forward current | δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 128 °C; square-wave pulse | 16 | | | А | |
| I _{FSM} | non-repetitive peak | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | 80 | | | А | |
| | forward current | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | 88 | | | Α | |
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| Static ch | aracteristics | | | | | | |
| V _F | forward voltage | I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u> | | - | 8.0 | 0.895 | V |
| Dynamic | characteristics | | | | ' | | |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; ramp recovery; Fig. 5; Fig. 7$ | - 20 25 | | 25 | ns | |
| Electrost | atic discharge | | | | | | |
| V_{ESD} | electrostatic discharge voltage | HBM; C = 250 pF; R = 1.5 kΩ | | - | - | 8 | kV |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|------------------------|--------------------|----------------|
| 1 | K | cathode | mb | |
| 2 | А | anode | 7 0 5 | K — A |
| mb | mb | mounting base; cathode | TO-220AC (SOD59) | 001aaa020 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | е | | | | |
|-------------|----------|---|---------|--|--|--|
| | Name | Description | Version | | | |
| BYW29E-100 | TO-220AC | plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC | SOD59 | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking codes |
|-------------|---------------|
| BYW29E-100 | BYW29E-100 |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Values | Unit |
|------------------|-------------------------------------|--|------------|------|
| V_{RRM} | repetitive peak reverse voltage | | 100 | V |
| V_{RWM} | crest working reverse voltage | | 100 | V |
| V_R | reverse voltage | | 100 | V |
| $I_{F(AV)}$ | average forward current | δ = 0.5 ; $T_{mb} \le$ 128 °C ;square-wave pulse; Fig. 1; Fig. 2 | 8 | А |
| I _{FRM} | repetitive peak forward current | $δ = 0.5$; $t_p = 25 \mu s$; $T_{mb} \le 128 °C$; square-wave pulse | 16 | А |
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | 80 | А |
| | | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | 88 | А |
| I _{RRM} | repetitive peak reverse current | $\delta = 0.001 \; ; t_p = 2 \; \mu s$ | 0.2 | А |
| I _{RSM} | non-repetitive peak reverse current | t _p = 100 μs | 0.2 | А |
| T _{stg} | storage temperature | | -40 to 150 | °C |
| T _j | junction temperature | | 150 | °C |
| Electrosta | atic discharge | | 1 | |
| V _{ESD} | electrostatic discharge voltage | HBM; C = 250 pF; R = 1.5 kΩ | 8 | kV |
| | | | | |

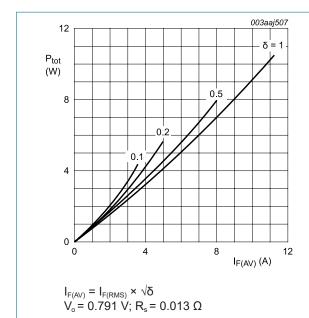
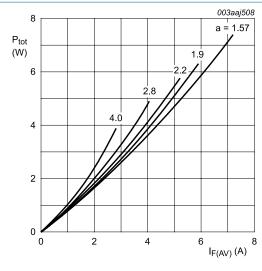


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 0.791 V; R_s = 0.013 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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Ultrafast power diode

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|-------------|-----|-----|-----|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 3 | - | - | 2.7 | K/W |
| $R_{\text{th(j-a)}}$ | thermal resistance from junction to ambient | in free air | - | 60 | - | K/W |

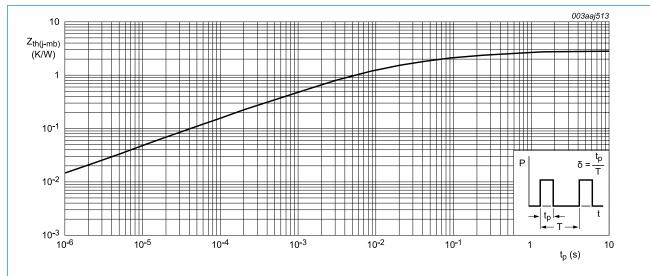


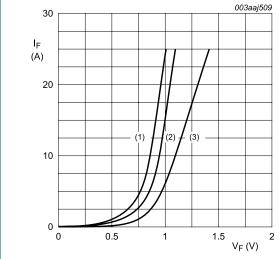
Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

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10. Characteristics

Table 7 Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------|--------------------------|--|-----|------|-------|------|
| Static cha | racteristics | | | | | |
| V _F | forward voltage | I _F = 8 A; T _j = 25 °C; <u>Fig. 4</u> | - | 0.92 | 1.05 | V |
| | | I _F = 20 A; T _j = 25 °C; <u>Fig. 4</u> | - | 1.1 | 1.3 | V |
| | | I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u> | - | 0.8 | 0.895 | V |
| I _R | reverse current | V _R = 100 V; T _j = 25 °C | - | 2 | 10 | μA |
| | | V _R = 100 V; T _j = 100 °C | - | 0.2 | 0.6 | mA |
| Dynamic | characteristics | | | | | |
| Q _r | recovered charge | $I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5; Fig. 6$ | - | 4 | 11 | nC |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; ramp recovery; Fig. 5; Fig. 7 | - | 20 | 25 | ns |
| | | $I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{R(meas)} = 0.25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ step recovery}; Fig. 8$ | - | 15 | 20 | ns |
| V _{FRM} | forward recovery voltage | I _F = 1 A; dI _F /dt = 10 A/μs; T _j = 25 °C; <u>Fig. 9</u> | - | 1 | - | V |



(1) T_i = 150 °C; typical values

(2) T_i = 150 °C; maximum values

(3) $T_i = 25$ °C; maximum values

 $V_o = 0.791 \text{ V}; R_s = 0.013 \Omega$

Fig. 4. Forward current as a function of forward voltage

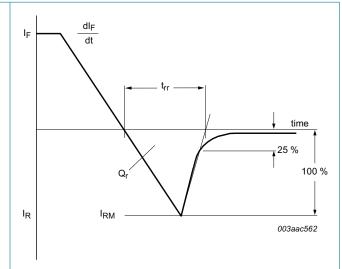
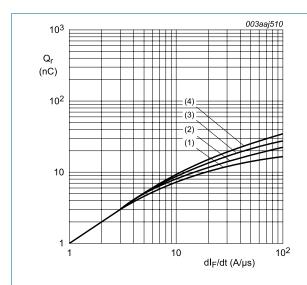


Fig. 5. Reverse recovery definitions; ramp recovery



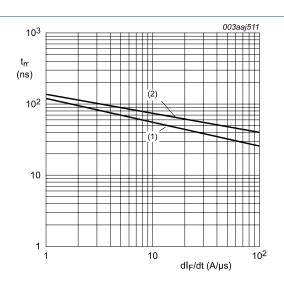
(1)
$$I_F = 1 A$$
; $T_j = 25 °C$

(2)
$$I_F = 2 A$$
; $T_i = 25 °C$

(3)
$$I_F = 5 A$$
; $T_j = 25 °C$

(4)
$$I_F = 10 \text{ A}$$
; $T_j = 25 \text{ °C}$

Fig. 6. Recovered charge as a function of rate of change of forward current; maximum values



(1)
$$I_F = 1 \text{ A}$$
; $T_j = 25 \text{ °C}$
(2) $I_F = 10 \text{ A}$; $T_i = 25 \text{ °C}$

Fig. 7. Reverse recovery time as a function of rate of change of forward current; maximum values

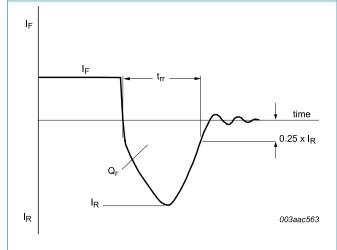


Fig. 8. Reverse recovery definitions; step recovery

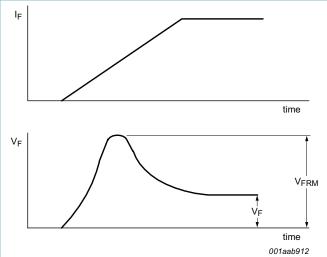
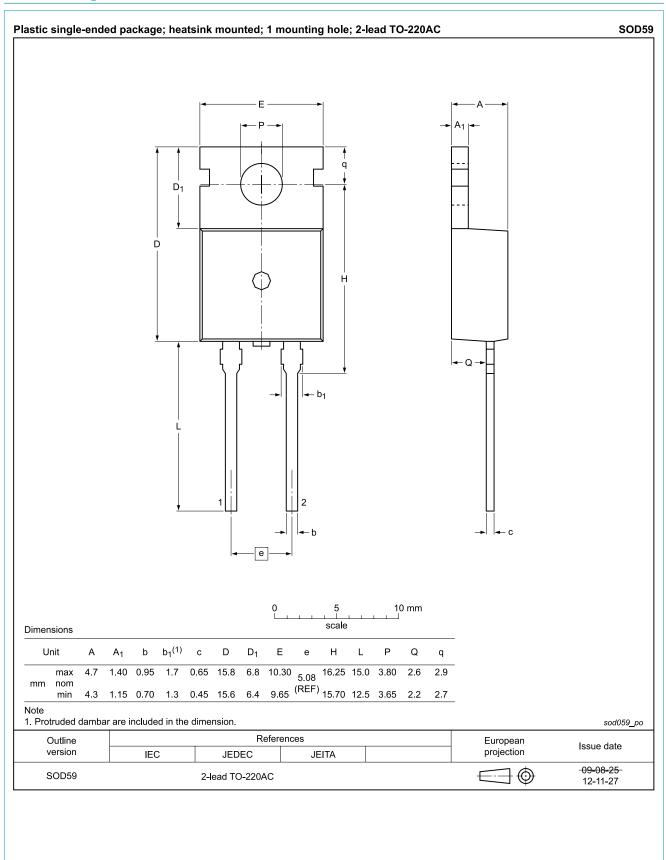


Fig. 9. Forward recovery definitions

11. Package outline



12. Legal information

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|--------------------------------------|--------------------|---|
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